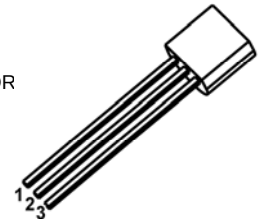
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

2SA608 TRANSISTOR (PNP)

TO-92

1. EMITTER
2. COLLECTOR
3. BASE



FEATURES

- Capable of being used in the low frequency to high frequency range.
- Large current capacity and wide ASO.

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-100	mA
P_C	Collector Power Dissipation	400	mW
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA, I_E=0	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-30			V
Emitter-Base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-25V, I_E=0			-1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V, I_C=0			-1	μA
DC current gain	h_{FE}	V_{CE}=-6V, I_C=-1mA	60		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-50mA, I_B=-5mA			-0.5	V
Transition frequency	f_T	V_{CE}=-6V, I_C=-10mA		180		MHz
Collector output capacitance	Cob	V_{CB}=-6V, f=1MHz		7		pF

CLASSIFICATION OF h_{FE}

Rank	D	E	F	G
Range	60-120	100-200	160-320	280-560